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Wickersham

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(54) **METHOD AND SYSTEM FOR MANUFACTURING BACK CONTACTS OF PHOTOVOLTAIC DEVICES**

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H01L 31/20	(2006.01)
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CPC ***H01L 31/022441*** (2013.01); ***C30B 1/023*** (2013.01); ***C30B 1/12*** (2013.01); ***C30B 29/48*** (2013.01); ***H01L 31/022425*** (2013.01); ***H01L 31/073*** (2013.01); ***H01L 31/1872*** (2013.01); ***H01L 31/20*** (2013.01); *Y02E 10/543* (2013.01); *Y02P 70/521* (2015.11)

(58) **Field of Classification Search**

None

See application file for complete search history.

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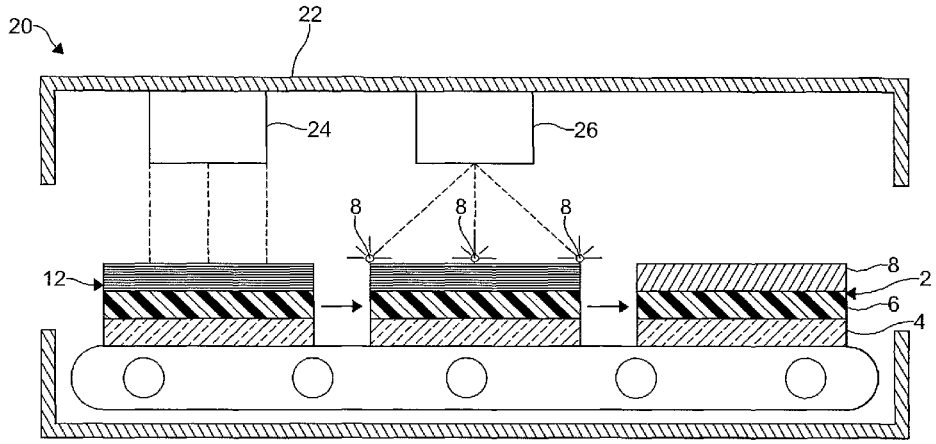
(57) **ABSTRACT**

A method for manufacturing a photovoltaic device includes a step of depositing one of an amorphous layer of ZnTe and a multilayer stack of Zn and Te adjacent a semiconductor layer. The one of the amorphous layer and the multilayer stack is then subjected to an energy impulse at a temperature equal to or greater than its critical temperature. The energy impulse results in an explosive crystallization to form a polycrystalline layer of ZnTe from the one of the amorphous layer and the multilayer stack.

14 Claims, 4 Drawing Sheets